

**IN74HC574A**

**Octal 3-State  
Noninverting D Flip-Flop  
High-Performance Silicon-Gate CMOS**

The IN74HC574A is identical in pinout to the LS/ALS574. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LS/ALSTTL outputs.

Data meeting the setup time is clocked to the outputs with the rising edge of the Clock. The Output Enable input does not affect the states of the flip-flops, but when Output Enable is high, all device outputs are forced to the high-impedance state; thus, data may be stored even when the outputs are not enabled.

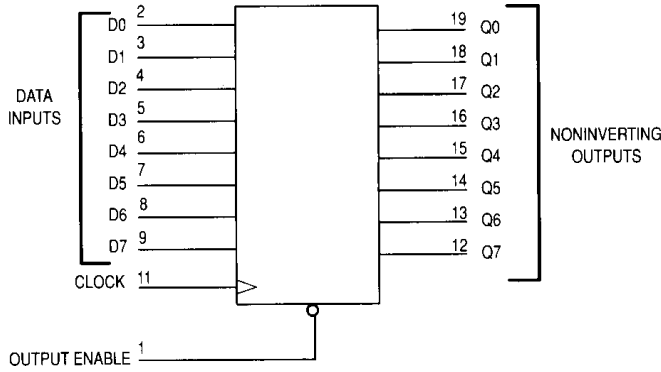
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0  $\mu$ A
- High Noise Immunity Characteristic of CMOS Devices

**N SUFFIX PLASTIC**

**DW SUFFIX SOIC**

**ORDERING INFORMATION**  
 IN74HC574AN Plastic  
 IN74HC574ADW SOIC  
 $T_A = -55^\circ$  to  $125^\circ$  C for all packages

**LOGIC DIAGRAM**



PIN 20 =  $V_{CC}$   
 PIN 10 = GND

**PIN ASSIGNMENT**

OUTPUT ENABLE	1	20	$V_{CC}$
D0	2	19	Q0
D1	3	18	Q1
D2	4	17	Q2
D3	5	16	Q3
D4	6	15	Q4
D5	7	14	Q5
D6	8	13	Q6
D7	9	12	Q7
GND	10	11	CLOCK

**FUNCTION TABLE**

Inputs		Output	
Output Enable	Clock	D	Q
L		H	H
L		L	L
L	L,H,	X	no change
H	X	X	Z

X = don't care  
 Z = high impedance

**MAXIMUM RATINGS\***

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage (Referenced to GND)	-1.5 to V <sub>CC</sub> +1.5	V
V <sub>OUT</sub>	DC Output Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>IN</sub>	DC Input Current, per Pin	±20	mA
I <sub>OUT</sub>	DC Output Current, per Pin	±35	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±75	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic DIP+ SOIC Package+	750 500	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

\*Maximum Ratings are those values beyond which damage to the device may occur.  
Functional operation should be restricted to the Recommended Operating Conditions.

+Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C  
SOIC Package: : - 7 mW/°C from 65° to 125°C

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V <sub>IN</sub> , V <sub>OUT</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)			
	V <sub>CC</sub> =2.0 V	0	1000	ns
	V <sub>CC</sub> =4.5 V	0	500	
	V <sub>CC</sub> =6.0 V	0	400	

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>IN</sub> and V<sub>OUT</sub> should be constrained to the range GND ≤ (V<sub>IN</sub> or V<sub>OUT</sub>) ≤ V<sub>CC</sub>.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

**DC ELECTRICAL CHARACTERISTICS**(Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	Guaranteed Limit			Unit
				25 °C to -55°C	≤85 °C	≤125 °C	
V <sub>IH</sub>	Minimum High-Level Input Voltage	V <sub>OUT</sub> =0.1 V or V <sub>CC</sub> -0.1 V   I <sub>OUT</sub>   ≤ 20 μA	2.0	1.5	1.5	1.5	V
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V <sub>IL</sub>	Maximum Low - Level Input Voltage	V <sub>OUT</sub> =0.1 V or V <sub>CC</sub> -0.1 V   I <sub>OUT</sub>   ≤ 20 μA	2.0	0.5	0.5	0.5	V
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V <sub>OH</sub>	Minimum High-Level Output Voltage	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>   I <sub>OUT</sub>   ≤ 20 μA	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
		6.0	5.9	5.9	5.9		
		V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>   I <sub>OUT</sub>   ≤ 6.0 mA   I <sub>OUT</sub>   ≤ 7.8 mA	4.5	3.98	3.84	3.7	
6.0	5.48	5.34	5.2				
V <sub>OL</sub>	Maximum Low-Level Output Voltage	V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub>   I <sub>OUT</sub>   ≤ 20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
		6.0	0.1	0.1	0.1		
		V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub>   I <sub>OUT</sub>   ≤ 6.0 mA   I <sub>OUT</sub>   ≤ 7.8 mA	4.5	0.26	0.33	0.4	
6.0	0.26	0.33	0.4				
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> =V <sub>CC</sub> or GND	6.0	±0.1	±1.0	±1.0	μA
I <sub>OZ</sub>	Maximum Three State Leakage Current	Output in High-Impedance State V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>OUT</sub> = V <sub>CC</sub> or GND	6.0	±0.5	±5.0	±10	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>IN</sub> =V <sub>CC</sub> or GND I <sub>OUT</sub> =0μA	6.0	4.0	40	160	μA

**AC ELECTRICAL CHARACTERISTICS**( $C_L=50\text{pF}$ , Input  $t_r=t_f=6.0\text{ ns}$ )

Symbol	Parameter	V <sub>CC</sub> V	Guaranteed Limit			Unit
			25 °C to -55°C	≤85°C	≤125°C	
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0	6.0	4.8	4.0	MHz
		4.5	30	24	20	
		6.0	35	28	24	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Clock to Q (Figures 1 and 4)	2.0	160	200	240	ns
		4.5	32	40	48	
		6.0	27	34	41	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)	2.0	150	190	225	ns
		4.5	30	38	45	
		6.0	26	33	38	
t <sub>PZH</sub> , t <sub>PZL</sub>	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)	2.0	140	175	210	ns
		4.5	28	35	42	
		6.0	24	30	36	
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0	60	75	90	ns
		4.5	12	15	18	
		6.0	10	13	15	
C <sub>IN</sub>	Maximum Input Capacitance	-	10	10	10	pF
C <sub>OUT</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State)	-	15	15	15	pF

C <sub>PD</sub>	Power Dissipation Capacitance (Per Enabled Output)	Typical @25°C, V <sub>CC</sub> =5.0 V			pF
	Used to determine the no-load dynamic power consumption: $P_D=C_{PD}V_{CC}^2f+I_{CC}V_{CC}$	24			

**TIMING REQUIREMENTS** ( $C_L=50\text{pF}$ , Input  $t_r=t_f=6.0\text{ ns}$ )

Symbol	Parameter	V <sub>CC</sub> V	Guaranteed Limit			Unit
			25 °C to -55°C	≤85°C	≤125°C	
t <sub>SU</sub>	Minimum Setup Time, Data to Clock (Figure 3)	2.0	50	65	75	ns
		4.5	10	13	15	
		6.0	9	11	13	
t <sub>H</sub>	Minimum Hold Time, Clock to Data (Figure 3)	2.0	5	5	5	ns
		4.5	5	5	5	
		6.0	5	5	5	
t <sub>w</sub>	Minimum Pulse Width, Clock (Figure 1)	2.0	75	95	110	ns
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>r</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Times (Figure 1)	2.0	1000	1000	1000	ns
		4.5	500	500	500	
		6.0	400	400	400	

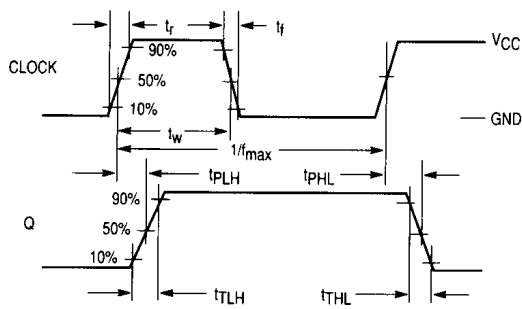


Figure 1. Switching Waveforms

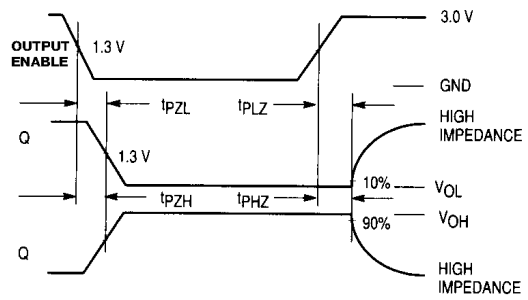


Figure 2. Switching Waveforms

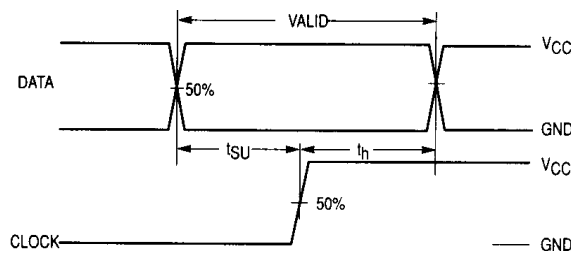
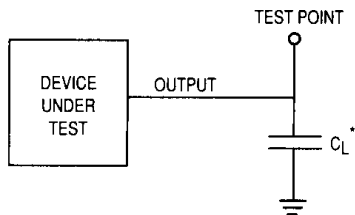
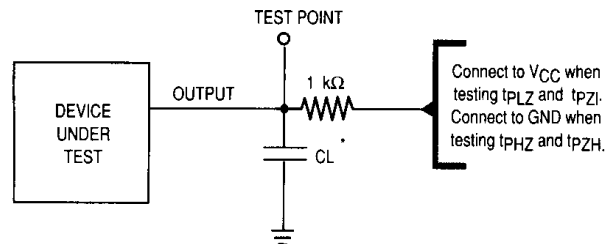


Figure 3. Switching Waveforms



\* Includes all probe and jig capacitance

Figure 4. Test Circuit



\*Includes all probe and jig capacitance

Figure 5. Test Circuit

EXPANDED LOGIC DIAGRAM

